

SHORT PROGRAM



21st International Conference on Molecular Beam Epitaxy

September 6-9, 2021

Virtual Conference

This series of successful conferences began in 1978 in Paris, and in recent years, has taken place in Nara, Japan (2012); Flagstaff, USA (2014); Montpellier, France (2016), and Shanghai, China (2018). The 21st International Conference on Molecular Beam Epitaxy will take place *virtually* in Puerto Vallarta, Mexico.

The International Conference on Molecular Beam Epitaxy provides a prominent international forum for reporting new developments in the areas of fundamental and applied molecular beam epitaxy research, including advances in the technique, synthesis of new materials, discovery of new physical properties, formation of novel heterostructures, and the development of innovative devices.



21st International Conference on Molecular Beam Epitaxy

SEPTEMBER 6 - 9, 2021

SCHEDULE	Monday, Sept 6	Tuesday, Sept 7	Wednesday, Sept 8	Thursday, Sept 9	
09:30 - 10:00	Opening Session	09:50 - 10:00 Prologue	09:50 - 10:00 Prologue	09:50 - 10:00 Prologue	
10:00 - 10:50	Plenary Anna Fontcuberta	Plenary James Speck	Al Cho MBE Award Charles Tu	Young Inv. MBE Award Stephanie Law	10:00 - 10:50
10:50 - 11:25	Invited Alexandre Arnoult	Invited Eva Benckiser	Invited Federico Panciera	Invited Gunther Springholz	10:50 - 11:25
11:25 - 12:00	Invited Joanna Millunchick	Invited Sergei V. Novikov	Invited Abderrauof Boucherif	Invited Peter Schüffelgen	11:25 - 12:00
12:00 - 12:15	Break	Break	12:00 - 12:30 Awards Ceremony	Break	12:00 - 12:15
12:15 - 12:50	Invited David Ritchie	Invited Matt Hardy		Invited Nitin Samarth	12:15 - 12:50
12:50 - 13:25	Invited Cheng Shang	Invited Alan Doolittle		Invited Matthew Barone	12:50 - 13:25
				Closing Session	13:25 - 13:45

18:30 - 19:05
19:05 - 19:40
19:40 - 20:15

Invited Hideki Yamamoto
Invited Shiro Tsukamoto
Invited Yuefeng Nie

18:30 - 19:05
19:05 - 19:40
19:40 - 20:15

American Central Daylight Savings Time (CDT, UTC -5) is used as a reference.

Wednesday night's session has been considered for the convenience of Asian countries.

The plenary and invited sessions consist of:

- 1) a prerecorded talk, available at the beginning of each session (max. 40min / 25 min), according to the schedule,
- 2) ten minutes of a live streaming session (embedded in Whova) after the prerecorded talk to answer written questions via the Whova platform's Q&A feature.

After the plenary and invited presentations, the prerecorded talks will be available to the attendees to benefit those in different time zones.

Pre-recorded oral and poster sessions will be available on demand during the conference.

The virtual Conference platform offers tools to easily interact with presenters through messaging and video conferencing.

[World clock and time converter](#)

COMMITTEES

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III-V Semiconductors

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II-VI, IV-VI, IV Semiconductors

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Nanostructures (Quantum Dots, Nanowires and Quantum Wells)

Richard Mirin, *National Institute of Standards and Technology, USA*, **Chair**

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Quantum Materials and Spintronics

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Heterogeneous Epitaxy and Integration

Richard Arès, *Université de Sherbrooke, Canada*, **Chair**

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Production MBE and Device Applications

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PLENARY SPEAKERS

Anna Fontcuberta i Morral, *EPFL, Switzerland*

Growth mechanisms of III-V and II-Vs : insights of the nanoscale

Jim Speck, *University of California - Santa Barbara, USA*

β -Ga₂O₃: Growth, Doping, and Device Design

INVITED SPEAKERS

Alexandre Arnoult, *LAAS-CNRS, Toulouse, France*

In-situ magnification inferred curvature measurement applied to dilute bismide growth

Matthew Barone, *Cornell University, USA*

An MBE Approach to Record-Breaking Millimeter-Wave Tunable Dielectrics

Eva Benckiser, *Max Planck Inst., Stuttgart, Germany*

Complex oxide interfaces: Mind the facet.

Abderraouf Boucherif, *Université de Sherbrooke, Canada*

Nanoscale substrate engineering for cost-effective III-V solar cells

W. Alan Doolittle, *Georgia Inst. of Technology, USA*

Chemical and Kinetic Mechanisms to Overcome Perceived Limitations in III-Nitride Epitaxy

Matthew Hardy, *Naval Research Laboratory, USA*

Growth of ScAlN: A Multi-functional Nitride

Stephanie Law, *University of Delaware, USA* **Young Investigator MBE Award**

Molecular Beam Epitaxy Growth of van der Waals films and nanostructures

Joanna Millunchick, *University of Michigan, USA*

Kinetics, Morphology, and Microstructure of III-V-Bi alloys

Yuefeng Nie, *Nanjing University, China*

Extreme tunability and novel functionality in ferroelectric oxide membranes

Sergei V. Novikov, *University of Nottingham, UK*

High-Temperature MBE of Hexagonal Boron Nitride for Deep-Ultraviolet, Lateral Heterostructures and Single-Photon Emitters

Federico Panciera, *C2N, Paris-Saclay, France*

Real-time TEM observations of III-V nanowire growth

David Ritchie, *University of Cambridge, UK*

Semiconductor quantum light sources using InAs quantum dots

Nitin Samarth, *Penn State University, USA*

Molecular Beam Epitaxy of Hybrid Topological Semimetal Heterostructures

Peter Schüffelgen, *FZ-Jülich, Germany*

From Materials to Devices: Topological Insulators for Quantum Computation

Chen Shang, *Univ. California - Santa Barbara, USA*

Robust high temperature operation of quantum dot lasers grown on (001) Si

Gunter Springholz, *Johannes Kepler Univ. Linz, Austria*

Natural Heterostructure Formation and Magnetic Doping of Bi- and Sb-Chalcogenide based Topological Insulators

Shiro Tsukamoto, *Univ. Electro-Communications, Japan*

Droplet epitaxy from beginning to present, pursuing initial cluster size

Charles W. Tu, *Univ. of California, San Diego, USA* **AI Cho MBE Award**

Bandgap Engineering and Device Applications of Dilute Nitrides

Hideki Yamamoto, *NTT Basic Research Lab., Japan*

Electron-Beam-Evaporation-Based Multi-Source Oxide MBE as a Synthesis Method for High-Quality and Novel Magnetic Materials - Beyond 3d Transition Metal Compounds

ORALS AND POSTERS

Oral and Poster presentations will be available on demand in the virtual Conference platform

OSMAw - candidate to the Outstanding Student MBE Award

	Topic	Title, Presenter	Note
ORAL ConfCode - 22	Heterogeneous Epitaxy and Integration	III-V/Si antiphase boundaries used as 2D-semimetallic topological vertical inclusions for solar hydrogen production Presenter: Charles Cornet <i>Institut FOTON – INSA Rennes, France</i>	
ORAL ConfCode - 23	Heterogeneous Epitaxy and Integration	Growth of Chalcogenide Perovskite Thin Films by Molecular Beam Epitaxy Presenter: Rafael Jaramillo <i>Massachusetts Institute of Technology, USA</i>	
ORAL ConfCode - 24	Heterogeneous Epitaxy and Integration	An integrated multi-step masking apparatus for molecular beam epitaxy system Presenter: William Holmes-Hewett <i>Victoria University of Wellington, New Zealand</i>	
ORAL ConfCode - 25	Heterogeneous Epitaxy and Integration	Molecular Beam Epitaxy of GaAs on NaCl Thin Films Presenter: Brelon May <i>NREL, U.S.A.</i>	
ORAL - OSMAw ConfCode - 26	Heterogeneous Epitaxy and Integration	Challenges of relaxed n-GaP on Si and strategies to reduce threading dislocation density Presenter: Ryan D. Hool <i>University of Illinois, United States</i>	
ORAL ConfCode - 27	Heterogeneous Epitaxy and Integration	Unraveling the dynamics of Van der Waals epitaxy of Ge over 2D graphene: New insights from in-situ transmission electron microscopy studies Presenter: Thierno Mamoudou Diallo <i>Université de Sherbrooke, Canada</i>	
ORAL ConfCode - 28	Heterogeneous Epitaxy and Integration	Anti-phase boundaries annihilation in the growth of GaSb on Silicon(001) Presenter: Jean-Baptiste Rodriguez <i>University of Montpellier – CNRS, France</i>	
ORAL ConfCode - 29	Heterogeneous Epitaxy and Integration	The annihilation of Antiphase Boundaries in GaAs growth on On-axis Si Substrate Presenter: Mingchu Tang <i>University College London, United Kingdom</i>	
ORAL ConfCode - 30	Heterogeneous Epitaxy and Integration	Narrow Excitonic Lines and Large-Scale Homogeneity of Transition-Metal Dichalcogenide Monolayers Grown by Molecular Beam Epitaxy on hBN Presenter: Wojciech Pacuski <i>University of Warsaw, Poland</i>	
POSTER ConfCode - 31	Heterogeneous Epitaxy and Integration	Van der Waals epitaxy of h-BN on few layers MoS₂ by plasma-assisted molecular beam epitaxy Presenter: Song Yu <i>National Dong Hwa University, Taiwan</i>	

POSTER ConfCode - 32	Heterogeneous Epitaxy and Integration	Molecular beam epitaxy and polarized excitonic emission of layered GaTe/GaAs thin films Presenter: Pavel Avdienko <i>Ioffe Institute, Russian Federation</i>	
POSTER ConfCode - 33	Heterogeneous Epitaxy and Integration	Investigation of GaAs MBE growth on FIB-treated Si(100) Presenter: Mikhail Eremenko <i>Southern Federal University, Russia</i>	
POSTER ConfCode - 34	Heterogeneous Epitaxy and Integration	Suppression of crack formation and propagation in strained SiGe by patterning Ge-on-Si substrates Presenter: Youya Wagatsuma <i>Tokyo City University, Japan</i>	
POSTER - OSMAw ConfCode - 35	Heterogeneous Epitaxy and Integration	Molecular Beam Epitaxy Growth of Transition Metal Dichalcogenide (Mo,Mn)Se₂ on 2D and polycrystalline substrates Presenter: Julia Kucharek <i>University of Warsaw, Poland</i>	
POSTER ConfCode - 36	Heterogeneous Epitaxy and Integration	Strong room-temperature EL emission from Ge-on-Si (111) diodes Presenter: Yuwa Sugiura <i>Tokyo City University, Japan</i>	
ORAL ConfCode - 37	III-V Semiconductors	Orientation Dependent Bi Incorporation in InAs Presenter: Brandon Carter <i>University of Michigan, USA</i>	
ORAL ConfCode - 38	III-V Semiconductors	Kinetic Model for Molecular Beam Epitaxy Growth of InAsSbBi Alloys Presenter: Stephen Schaefer <i>Arizona State University, United States</i>	
ORAL - OSMAw ConfCode - 39	III-V Semiconductors	Remote heteroepitaxy of In(x)Ga(1-x)As on GaAs Presenter: Tobias Henksmeier <i>Paderborn University, Germany</i>	
ORAL - OSMAw ConfCode - 40	III-V Semiconductors	Crystallographic tilt in coherently strained InAsSbBi grown on (100) GaSb substrates offcut toward [011] Presenter: Marko Milosavljevic <i>Arizona State University, USA</i>	
ORAL ConfCode - 41	III-V Semiconductors	Photoluminescence and Minority Carrier Lifetime of Quinary GaInAsSbBi Alloys Grown by Molecular Beam Epitaxy Presenter: Rigo Carrasco <i>Air Force Research Laboratory, USA</i>	
ORAL ConfCode - 42	III-V Semiconductors	Recombination Rate Analysis and Photodetector Performance of InGaAs/InAsSb Superlattices Grown by Molecular Beam Epitaxy Presenter: Rigo Carrasco <i>Air Force Research Laboratory, USA</i>	
ORAL ConfCode - 43	III-V Semiconductors	Multi-category classification of RHEED patterns using deep learning Presenter: Jinkwan Kwoen <i>The University of Tokyo, Japan</i>	
ORAL - OSMAw ConfCode - 44	III-V Semiconductors	Effects of tensile and compressive strain on epitaxial GaN_xP grown on Si with post-growth annealing and hydrogenation. Presenter: Srinath Murali <i>Arizona State University, USA</i>	

ORAL ConfCode - 45	III-V Semiconductors	Real-time Reflectance Anisotropy Spectroscopy of GaAs Epitaxial Growth: Temperature-Induced As vacancies Presenter: Jorge Ortega-Gallegos <i>Universidad Autónoma de San Luis Potosí, México</i>	
ORAL - OSMaw ConfCode - 46	III-V Semiconductors	Doping Assessment of Ga-assisted MBE Grown Be-Doped GaAs and Te-Doped GaAsSb Nanowires. Presenter: Priyanka Ramaswamy <i>North Carolina A&T State University, USA</i>	
ORAL ConfCode - 47	III-V Semiconductors	Chemical beam epitaxy of GaP_{1-x}N_x alloys and GaP_{1-x}N_x/GaP_{1-y}As_y short-period superlattices on nominally (001)-oriented GaP-on-Si substrates Presenter: Karim Ben Saddik <i>Universidad Autónoma de Madrid, Spain</i>	
ORAL ConfCode - 48	III-V Semiconductors	Optimization of AlGaAsSb growth on lattice matched InGaAs on InP Substrates by MBE Presenter: Pallavi Patil <i>EPSRC National Epitaxy Facility, University of Sheffield, UK</i>	
ORAL - OSMaw ConfCode - 49	III-V Semiconductors	A study of Epitaxial GaAsSbN (Te) ensemble nanowires for near-infrared region photodetection. Presenter: Rabin Pokharel <i>North Carolina A&T State University, USA</i>	
ORAL - OSMaw ConfCode - 50	III-V Semiconductors	Examination of the Optical Properties of GaSb_{1-x}Bi_x by Spectroscopic Ellipsometry Presenter: John H. McElearney <i>Tufts University, USA</i>	
ORAL - LATE NEWS - OSMaw ConfCode - 51	III-V Semiconductors	Strain Balancing for InAs Based ICL growth Presenter: Maximilian Beiser <i>TU Wien, Austria</i>	
POSTER - OSMaw ConfCode - 52	III-V Semiconductors	Alternative for ultraviolet disinfection. Cubic and hexagonal AlGaIn-based UVC-LED challenges Presenter: Horacio Solís-Cisneros <i>Tecnológico Nacional de México/Instituto Tecnológico de Tuxtla Gutiérrez, México</i>	
POSTER - OSMaw ConfCode - 53	III-V Semiconductors	GaN growth on (0 0 1) and (1 1 0) MgO under different Ga/N ratios by MBE Presenter: Kevin Meyer <i>Clausthal University of Technology, Germany</i>	
POSTER ConfCode - 54	III-V Semiconductors	Growth of 6.2 Å semiconductor topological materials on lattice engineered virtual substrates Presenter: Heather Haugan <i>Air Force Research Laboratories, USA</i>	
POSTER ConfCode - 55	III-V Semiconductors	Impact of As₂ pressure on the molecular beam epitaxial growth of AlGaAs superlattice at temperature over 700? Presenter: Reiji Suzuki <i>Ehime University, Japan</i>	
POSTER ConfCode - 56	III-V Semiconductors	Indium Accumulation in Self-assembled Nanoholes in GaAs(001) Surfaces Presenter: Shiro Tsukamoto <i>The University of Electro-Communications, Japan</i>	
POSTER - OSMaw ConfCode - 57	III-V Semiconductors	Relating as-grown surface morphologies to electron transport properties in high mobility InSb quantum wells Presenter: Erik Cheah <i>ETH Zürich, Switzerland</i>	

POSTER - OSMAw ConfCode - 58	III-V Semiconductors	Hyperbolic-tan graded composition $\text{In}_x\text{Ga}_{1-x}\text{As}$ layers for THz radiation emitters Presenter: Alfredo Belio Manzano <i>Universidad Autónoma de San Luis Potosí, México</i>	
ORAL ConfCode - 59	II-VI, IV-VI, IV Semiconductors	Elucidation of the origin of double-peak emission of epitaxial CdSe/ZnSe fractional monolayer quantum dots Presenter: Carlos Basilio-Ortiz <i>Cinvestav-IPN, Mexico</i>	
ORAL ConfCode - 60	II-VI, IV-VI, IV Semiconductors	MBE of stoichiometric Tin-Telluride thin films Presenter: Tsuboi Kaito <i>Waseda Univ., Japan</i>	
ORAL - OSMAw ConfCode - 61	II-VI, IV-VI, IV Semiconductors	Crystal Quality Improvement of ZnTe (110) Thin Film Prepared on Sapphire by Increasing the Nuclei Density on the Substrate Surface Presenter: Shotaro Kobayashi <i>Waseda University, Japan</i>	
ORAL - OSMAw ConfCode - 62	II-VI, IV-VI, IV Semiconductors	Effects of CBr_4 in Growth of GeSn(C) Presenter: Tuhin Dey <i>Texas State University, USA</i>	
ORAL - OSMAw ConfCode - 63	II-VI, IV-VI, IV Semiconductors	Epitaxial lift-off monocrystalline CdTe/MgCdTe double heterostructures and proton radiation study for space applications Presenter: Jia Ding <i>Arizona State University, USA</i>	
ORAL ConfCode - 64	II-VI, IV-VI, IV Semiconductors	Adsorption kinetics of selenium and tellurium monitored by a heated quartz crystal microbalance Presenter: Maria Hilse <i>The Pennsylvania State University, USA</i>	
ORAL - OSMAw ConfCode - 65	II-VI, IV-VI, IV Semiconductors	Effects of Atomic H on $\text{Ge}_{1-x}\text{C}_x$ Grown Using Hybrid Source Molecular Beam Epitaxy Presenter: Md. Shamim Reza <i>Texas State University, USA</i>	
POSTER ConfCode - 66	II-VI, IV-VI, IV Semiconductors	Tuning the excitonic emission of nearly lattice-matched $\text{Zn}_{1-y}\text{Mg}_y\text{Se}/\text{Zn}_{1-x}\text{Cd}_x\text{Se}/\text{Zn}_{1-z}\text{Cd}_z\text{Se}/\text{Zn}_{1-x}\text{Cd}_x\text{Se}/\text{Zn}_{1-y}\text{Mg}_y\text{Se}$ ($z > x$) quantum wells in the yellow-green range Presenter: Gerardo Villa <i>Instituto Politécnico Nacional, Mexico</i>	
POSTER ConfCode - 67	II-VI, IV-VI, IV Semiconductors	Fabrication of High-Quality and Strain-Relaxed GeSn Microdisks by Integrating Selective Epitaxial Growth and Selective Wet Etching Methods Presenter: Zuimin Jiang <i>Fudan University, China</i>	
POSTER - OSMAw ConfCode - 68	II-VI, IV-VI, IV Semiconductors	Investigations of Annealed GeSn Layer Grown by Molecular Beam Epitaxy (MBE) as Virtual Substrate for Group-IV Optoelectronic Devices Presenter: Hui Jia <i>University College London, UK</i>	
POSTER ConfCode - 69	II-VI, IV-VI, IV Semiconductors	Epitaxial growth of strained $\text{Si}_{0.2}\text{Ge}_{0.8}$ on Ge microbridge Presenter: Takahiro Inoue <i>Tokyo City Univ., Japan</i>	

ORAL ConfCode - 70	MBE Fundamentals	Is a substrate miscut really required for high quality III-V/Si monolithic integration? Presenter: Charles Cornet <i>Institut FOTON – INSA Rennes, France</i>	
ORAL ConfCode - 71	MBE Fundamentals	A novel optoelectronic materials family: epitaxy of GaSe and InSe van der Waals heterostructures Presenter: Marcel S. Claro <i>International Iberian Nanotechnology Laboratory, Portugal</i>	
ORAL ConfCode - 72	MBE Fundamentals	Van der Waals epitaxy of two-dimensional β-In₂Se₃ Presenter: Marcel S. Claro <i>International Iberian Nanotechnology Laboratory, Portugal</i>	
ORAL ConfCode - 73	MBE Fundamentals	Drastic Effect of Azimuthal Cell Arrangement on the Luminescence Efficiency of Nanowire Shells Presenter: Lutz Geelhaar <i>Paul-Drude-Institut für Festkörperelektronik, Leibniz-Institut im Forschungsverbund Berlin e.V., Germany</i>	
ORAL ConfCode - 74	MBE Fundamentals	Impact of Bi on breakdown of epitaxy of low temperature GaAs:Bi Presenter: Esperanza Luna <i>Paul-Drude-Institut für Festkörperelektronik, Germany</i>	
ORAL ConfCode - 75	MBE Fundamentals	Thermal Laser Epitaxy - Promises and Results Presenter: Wolfgang Braun <i>Max Planck Institute for Solid State Research, Germany</i>	
ORAL ConfCode - 76	MBE Fundamentals	Thermal Laser Epitaxy of ultrapure refractory-metal thin films Presenter: Sander Smink <i>Max Planck Institute for Solid State Research, Germany</i>	
ORAL - OSMaW ConfCode - 77	MBE Fundamentals	Molecular Beam Epitaxy growth of MoTe₂ on Hexagonal Boron Nitride Presenter: Bartłomiej Seredyński <i>University of Warsaw, Poland</i>	
ORAL - OSMaW ConfCode - 78	MBE Fundamentals	Molecular Beam Epitaxy of a 2D material nearly lattice matched to a 3D substrate: NiTe₂ on GaAs Presenter: Bartłomiej Seredyński <i>University of Warsaw, Poland</i>	
ORAL ConfCode - 79	MBE Fundamentals	Real-time, In-situ Flux Monitoring: A Revolutionary New Development in Solid-Source Molecular Beam Epitaxy Presenter: James Gupta <i>University of Ottawa, Canada</i>	
POSTER ConfCode - 80	MBE Fundamentals	Surface Step Contribution to GaAs (001) Reflectance-Anisotropy Spectra Presenter: Alfonso Lastras-Martínez <i>Universidad Autónoma de San Luis Potosí, México</i>	
POSTER - OSMaW ConfCode - 81	MBE Fundamentals	An Alternative Approach for the Molecular Beam Epitaxy of the Heavy Fermion Compound YbRh₂Si₂ Presenter: Emine Bakali <i>TU Wien, Austria</i>	
ORAL ConfCode - 82	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	InAs/InP/GaAsSb core-dual-shell nanowires: growth, strain relaxation and carrier separation Presenter: Valentina Zannier <i>NEST – Scuola Normale Superiore and Istituto Nanoscienze – CNR, Italy</i>	

ORAL - OSMAw ConfCode - 83	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Morphology control and electrical characterization of free-standing InSb nanostructures Presenter: Isha Verma <i>NEST – Scuola Normale Superiore and Istituto Nanoscienze – CNR, Italy</i>	
ORAL ConfCode - 84	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Self-catalyzed InSb/InAs Quantum Dot Nanowires Presenter: Omer Arif <i>Istituto Nanoscienze-CNR and Scuola Normale Superiore, Italy</i>	
ORAL ConfCode - 85	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Molecular Beam Epitaxial Growth of GaAs/GaNAsBi/GaAs Core-Multishell Nanowires Presenter: Yuto Torigoe <i>Ehime University, Japan</i>	
ORAL ConfCode - 86	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Tuning the density of self-assembled GaN nanowires over three orders of magnitude with Si seeds on metallic TiN Presenter: Thomas Auzelle <i>Paul-Drude-Institut, Germany</i>	
ORAL ConfCode - 87	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Metamorphic InAs/InGaAs QWs with electron mobilities exceeding $7 \times 10^5 \text{cm}^2/\text{Vs}$ Presenter: Giorgio Biasiol <i>CNR, Italy</i>	
ORAL ConfCode - 88	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	The formation of In islands on GaAs(111)A in the wide temperature range Presenter: Artur Tuktamyshev <i>INFN, Italy</i>	
ORAL ConfCode - 89	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Ehrlich-Schwöbel barrier effect on the Ga droplet nucleation on singular and vicinal GaAs(111)A Presenter: Artur Tuktamyshev <i>INFN, Italy</i>	
ORAL - OSMAw ConfCode - 90	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Highly uniform GaSb quantum dots based on local droplet etching on AlGaSb Presenter: Joonas Hilska <i>Tampere University, Finland</i>	
ORAL - OSMAw ConfCode - 91	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Al(x)Ga(1-x)As /Al(y)Ga(1-y)As axial short-period superlattices in self-catalyzed nanowires Presenter: Donovan Hilliard <i>Helmholtz-Zentrum Dresden-Rossendorf, Germany</i>	
ORAL ConfCode - 92	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Metamorphic buffer layer platform for 1550 nm single-photon sources Presenter: Fauzia Jabeen <i>University of Würzburg, Germany</i>	
ORAL ConfCode - 93	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Highly uniform selective area epitaxy of non-VLS GaAsSb:Si nanowires Presenter: Akhil Ajay <i>Walter Schottky Institute, Technical University of Munich, Germany</i>	
ORAL - OSMAw ConfCode - 94	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Wurtzite phase control of self-assisted GaAs nanowires grown by molecular beam epitaxy Presenter: Thomas Dursap <i>INL, France</i>	

ORAL - OSMAw ConfCode - 95	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Ferromagnetic Fe-doped GaSb quantum dots with high Curie temperature Presenter: Sriharsha Karumuri <i>University of Tokyo, Japan</i>	
ORAL ConfCode - 96	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Growth of Site-Controlled InAs/GaAs Quantum Dot Arrays for Integration into Photonic Devices Presenter: Charlotte Ovenden <i>University of Sheffield, UK</i>	
ORAL - OSMAw ConfCode - 97	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Self-Assembly of Tensile-Strained InGaAs Quantum Dots on InAs(111)A Presenter: Kevin Vallejo <i>Boise State University, U.S.</i>	
POSTER ConfCode - 98	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	The role of growth temperature on the composition and electronic properties of InAs/In_xGa_{1-x}As selective area grown nanowires Presenter: Daria Beznasyuk <i>University of Copenhagen, Denmark</i>	
POSTER ConfCode - 99	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Surfactant effect of Bi during InAs quantum dot growth on InP(311)B substrates by molecular beam epitaxy Presenter: Kouichi Akahane <i>National Institute of Information and Communications Technology, Japan</i>	
POSTER ConfCode - 100	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Nucleation mechanism of GaAs nanowires on Si(111) substrates by constituent Ga self-catalyzed molecular beam epitaxy Presenter: Ryo Murakami <i>Ehime University, Japan</i>	
POSTER ConfCode - 101	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Evolution of Lateral InSb Nanowires on (001) CdTe Substrate Presenter: Suwit Kiravittaya <i>Chulalongkorn University, Thailand</i>	
POSTER - OSMAw ConfCode - 102	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Low Areal Densities of InAs Quantum Dots on GaAs(100) Prepared by Molecular Beam Epitaxy Presenter: Akshay Kumar Verma <i>Paderborn University, Germany</i>	
POSTER ConfCode - 103	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Effect of the Number of Stacks on the 2D to 3D Transition of Stacked Submonolayer (SML) InAs Nanostructures Presenter: Itaru Kamiya <i>Toyota Technological Institute, Japan</i>	
POSTER - OSMAw ConfCode - 104	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	SELECTIVE AREA GROWTH OF InP NANOWIRES ON Si NANOTIPS BY MOLECULAR BEAM EPITAXY Presenter: Anagha Kamath <i>Humboldt University, Germany</i>	
POSTER ConfCode - 105	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Telecom wavelength InP based quantum dots: Growth and characterization Presenter: Ranbir Kaur <i>University of Kassel, Germany</i>	
POSTER ConfCode - 106	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Effect of Nanohole Size and Density on the Optical Properties of Positioned InAs/GaAs Quantum Dots Presenter: Aristotelis Trapalis <i>The University of Sheffield, United Kingdom</i>	

POSTER ConfCode - 107	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	CuInSe₂ nanostructures grown by MBE Presenter: Alessandro Cavalli <i>INL, Portugal</i>	
POSTER ConfCode - 108	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	GaAs islands grown on InGaAs by droplet epitaxy Presenter: Stephanie Tomasulo <i>U.S. Naval Research Laboratory, United States</i>	
POSTER - OSMAw ConfCode - 109	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Control of InAs/GaAs QD properties through the use of a Bi surfactant Presenter: Nicholas Bailey <i>The University of Sheffield, UK</i>	
POSTER ConfCode - 110	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Full wafer control of local droplet etched GaAs quantum dots Presenter: Hans-Georg Babin <i>Ruhr-Universität Bochum, Germany</i>	
POSTER ConfCode - 111	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Wafer Scale Density Modulation of Self-Assembled Quantum Dots by Epitaxial Surface Roughness Control Presenter: Nikolai Bart <i>Ruhr-Universität Bochum, Germany</i>	
POSTER - OSMAw ConfCode - 112	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Selective area growth of GaN nanowires on sapphire and graphene substrates by molecular beam epitaxy Presenter: Yang Li <i>NTNU, Norway</i>	
POSTER ConfCode - 113	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Broadband Emission from Stacked InAs Quantum Dots Embedded with GaAs Layers Under Various Growth Rates for Broadband Light Source Applications Presenter: Nobuhiko Ozaki <i>Wakayama Univ., Japan</i>	
POSTER ConfCode - 114	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Tailorable Growth of Self-catalyzed GaP Nanowires on Template-free Si Substrates Presenter: Yury Berdnikov <i>St. Petersburg State University, Russia</i>	
POSTER ConfCode - 115	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Low-Density Arrays of Small-Size Nanostructures Controlled by Two-Stage Arsenic Exposure during Droplet Epitaxy Presenter: Sergey Balakirev <i>Southern Federal University, Russia</i>	
POSTER - OSMAw ConfCode - 116	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Punctuated Growth of InAs Qdashes-in-a-Well for enhanced 2 μm emission Presenter: Rafael Jumar Chu <i>Korea Institute of Science and Technology; University of Science and Technology, South Korea</i>	
POSTER - OSMAw ConfCode - 117	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Growth of near-surface InAs 2D-channels on pseudomorphic buffer layers Presenter: William Strickland <i>New York University, NY</i>	
POSTER ConfCode - 118	Nanostructures (Quantum Dots, Nanowires and Quantum Wells)	Influence of In Segregation on InAs Quantum Dots Growth in Dot-in-a-Well Presenter: Nobuhiko Ozaki <i>Wakayama Univ., Japan</i>	

ORAL ConfCode - 119	Nitrides	Suppression of parasitic Conductivity in ultra-pure GaN/AlGaN Heterostructures by Carbon delta-Doping Presenter: Stefan Schmult <i>TU Dresden, Germany</i>	
ORAL ConfCode - 120	Nitrides	High-quality Sc_xAl_{1-x}N layers (0 < x ≤ 0.25) grown on (0001) GaN templates using MBE Presenter: Duc Dinh <i>Paul-Drude-Institut für Festkörperelektronik, Germany</i>	
ORAL ConfCode - 121	Nitrides	Carbon-related yellow and blue Luminescence in GaN Presenter: Hannes Schürmann <i>University of Magdeburg, Germany</i>	
ORAL ConfCode - 122	Nitrides	Effect of The AlGa_xN Capping Layer on the Emission Properties of InGa_xN Quantum Wellson Properties of InGa_xN Quantum Wells Presenter: Stefano Vichi <i>INFN, Italy</i>	
ORAL - OSMaw ConfCode - 123	Nitrides	First Time Achievement of MME Grown P-type AlN:Be Films Presenter: Habib Ahmad <i>Georgia Institute of Technology, United States</i>	
ORAL - OSMaw ConfCode - 124	Nitrides	Growth of epitaxial NbN-AlN superconductor/metal-semiconductor heterostructures by molecular beam epitaxy Presenter: John G Wright <i>Cornell University, USA</i>	
ORAL - OSMaw ConfCode - 125	Nitrides	Metal Rich, Low Temperature MME Growth of Aluminum Indium Nitride in the Entire Composition Range Presenter: Zachary Engel <i>Georgia Tech, USA</i>	
ORAL ConfCode - 126	Nitrides	Performance and limitations of blue InGa_xN QWs by plasma-assisted MBE Presenter: Sebastian Tamariz <i>EPFL, CRHEA, CNRS, Switzerland France</i>	
ORAL - OSMaw ConfCode - 127	Nitrides	Structural investigation of self-assembled InGa_xN/GaN superlattice grown on GaN template by plasma-assisted molecular beam epitaxy Presenter: Kamruzzaman Khan <i>Univ. of Michigan, Washtenaw, USA</i>	
ORAL - OSMaw ConfCode - 128	Nitrides	Epitaxial Sc_xAl_{1-x}N : Structural, Chemical, Electrical Properties, and Ferroelectric Behavior Presenter: Joseph Casamento <i>Cornell University, U.S.A</i>	
POSTER ConfCode - 129	Nitrides	Direct epitaxial growth of SmN on (100)Si Presenter: Eva-M. Anton <i>Victoria University of Wellington, New Zealand</i>	
POSTER ConfCode - 130	Nitrides	Epitaxial growth of rare earth nitrides on lanthanum aluminate Presenter: William Holmes-Hewett <i>Victoria University of Wellington, New Zealand</i>	
POSTER ConfCode - 131	Nitrides	Wavelength-dependent Conductivity of photo-generated 2DEGs in ultra-pure GaN/AlGa_xN Heterostructures Presenter: Thomas Mikolajick <i>TU Dresden & NaMLab gGmbH, Germany</i>	

POSTER ConfCode - 132	Nitrides	Room temperature layer-by-layer heteroepitaxy of Gd metal and subsequent nitridation Presenter: Jay Chan <i>Victoria University of Wellington, New Zealand</i>	
POSTER - OSMaw ConfCode - 133	Nitrides	Investigation of Phase Composition in PAMBE Grown NbN_x Thin Films Presenter: Austin Thomas <i>University of Maryland, USA</i>	
POSTER - OSMaw ConfCode - 134	Nitrides	Self-Assembled AlGa_N Superlattices Grown Via Metal Modulated Epitaxy Presenter: Zachary Engel <i>Georgia Tech, USA</i>	
POSTER - OSMaw ConfCode - 135	Nitrides	Kinetic Modeling of Vertical Indium Segregation During InGa_N Epitaxy Presenter: Christopher Matthews <i>Georgia Institute of Technology, USA</i>	
POSTER - OSMaw ConfCode - 136	Nitrides	Evolution of Raman Modes of InN Thin Films Grown with Varying III/V ratio by PA-MBE Presenter: Balkrishna Choubey <i>Indian Institute of Technology Jammu, India</i>	
ORAL ConfCode - 137	Oxides	RF Device Performance of Ga₂O₃ Field-Effect Transistors Grown on Ga₂O₃ (010) Substrates by Plasma-Assisted MBE Presenter: Takafumi Kamimura <i>National Institute of Information and Communications Technology, Japan</i>	
ORAL ConfCode - 138	Oxides	Oxide Films Grown by Thermal Laser Epitaxy Presenter: Dong Yeong Kim <i>Max Planck Institute for Solid State Research, Germany</i>	
ORAL - OSMaw ConfCode - 139	Oxides	A Modified Silicon Effusion Cell for Controlled Silicon Donor Doping in beta-Ga₂O₃ in Plasma-assisted MBE Presenter: Jonathan McCandless <i>Cornell, USA</i>	
ORAL - LATE NEWS - OSMaw ConfCode - 140	Oxides	Growth and Characterization of InSb_{1-x}Bi_x: A (Potentially) Not So Highly Mismatched Alloy for Wavelength Extension on InSb Presenter: Corey White <i>The University of Texas at Austin, USA</i>	
ORAL - LATE NEWS - OSMaw ConfCode - 141	Oxides	Efficient and Unexpected Suboxide Sources in Oxide MBE Presenter: Georg Hoffmann <i>Paul-Drude-Institut, Germany</i>	
POSTER ConfCode - 142	Oxides	Enhanced thermodynamic stability of Cu oxides via tuning kinetic conditions Presenter: Yoshiko Nanao <i>University of St Andrews, United Kingdom</i>	
ORAL ConfCode - 143	Production MBE and Device Applications	Tuning the Charge Transfer Dynamics in the MBE-grown Ga_N Nanowires for Efficient Photoelectrochemical Ultraviolet Photodetection Presenter: Danhao Wang <i>University of Science and Technology of China, China</i>	
ORAL - OSMaw ConfCode - 144	Production MBE and Device Applications	Platinum Nanoparticle-decorated AlGa_N Nanowires for Self-powered High Responsivity Solar-blind Photodetection Presenter: Danhao Wang <i>University of Science and Technology of China, China</i>	

ORAL - OSMAw ConfCode - 145	Production MBE and Device Applications	The Impact of InGaAs Absorber Thickness on Intervalley Extraction in Hot Carrier Solar Cells Presenter: Kyle Dorman <i>University Of Oklahoma, USA</i>	
ORAL - OSMAw ConfCode - 146	Production MBE and Device Applications	Photodetector based on vertical (In,Ga)N nanowires grown by molecular beam epitaxy Presenter: Jianya Zhang <i>Suzhou Institute of Nano-Tech and Nano-Bionics (SINANO), Chinese Academy of Sciences (CAS), China</i>	
ORAL ConfCode - 147	Production MBE and Device Applications	Co-integration of enhancement mode and depletion mode Al(Ga)N/GaN high electron mobility transistors using p-GaN sublimation and local area regrowth by molecular beam epitaxy Presenter: Yvon CORDIER <i>Univ. Côte d'Azur, France</i>	
ORAL - OSMAw ConfCode - 148	Production MBE and Device Applications	MBE-grown low threshold InAs-based interband cascade lasers Presenter: Kedong Zhang <i>Nanjing University, China</i>	
ORAL ConfCode - 149	Production MBE and Device Applications	GaAsBi Multiple Quantum Well Photovoltaics: Trade-off Between Carrier Collection and Light Absorption Presenter: Thomas Rockett <i>University of Sheffield, UK</i>	
ORAL ConfCode - 150	Production MBE and Device Applications	Growth of Thick GaAsBi Diodes for Detectors Presenter: Robert Richards <i>The University of Sheffield, UK</i>	
ORAL - OSMAw ConfCode - 151	Production MBE and Device Applications	InP-based quantum dot lasers emitting at 1.3 μm Presenter: Vinayakrishna Joshi <i>Institute of Nanostructure Technology and Analytics (INA), Germany</i>	
ORAL ConfCode - 152	Production MBE and Device Applications	Efficient Mid-IR (3–4 μm) Metamorphic InSb/InAs/In(Ga,Al)As Diode Heterostructures Grown on GaAs(001) Substrates Presenter: Mikhail Chernov <i>Ioffe Institute, Russian Federation</i>	
ORAL - OSMAw ConfCode - 153	Production MBE and Device Applications	InP quantum dot and InGaP quantum well visible lasers on Si Presenter: Pankul Dhingra <i>University of Illinois at Urbana-Champaign, USA</i>	
ORAL ConfCode - 154	Production MBE and Device Applications	Sb-based Mid-IR lasers grown by MBE on Silicon(001) Presenter: Laurent Cerutti <i>University of Montpellier, France</i>	
ORAL - OSMAw ConfCode - 155	Production MBE and Device Applications	Investigation of Impact Ionization in Digital and Random Alloy AlGaAsSb Avalanche Photodiodes on InP Substrates Presenter: Seunghyun Lee <i>The Ohio State University, USA</i>	
POSTER ConfCode - 156	Production MBE and Device Applications	A comparison of different passivation layers for GaInAs solar cells grown by solid-source molecular beam epitaxy Presenter: Ryuji Oshima <i>National Institute of Advanced Science and Technology, Japan</i>	

POSTER ConfCode - 157	Production MBE and Device Applications	MBE-grown GaAs_xP_{1-x}/Si photoelectrodes for solar hydrogen production Presenter: Mekan Piriye <i>INSA Rennes, France</i>	
POSTER - OSMAw ConfCode - 158	Production MBE and Device Applications	INFLUENCE OF THE In CONTENT AND SURFACE RECONSTRUCTION ON THE PROPERTIES OF SUBMONOLAYER QUANTUM DOT INFRARED PHOTODETECTORS Presenter: Ahmad Alzeidan <i>University of Sao Paulo, Brazil</i>	
ORAL - OSMAw ConfCode - 159	Quantum Materials and Spintronics	Growth Optimization of Van der Waals Epitaxy of Bi₂Se₃ Presenter: Zhengtianye Wang <i>University of Delaware, U.S.A.</i>	
ORAL ConfCode - 160	Quantum Materials and Spintronics	Large-area van der Waals epitaxy of Fe₃GeTe₂ ferromagnetic films on graphene Presenter: João Marcelo J. Lopes <i>Paul-Drude-Institute, Germany</i>	
ORAL ConfCode - 161	Quantum Materials and Spintronics	Room-temperature spin injection and spin-to-charge conversion in a ferromagnetic semiconductor / topological insulator heterostructure Presenter: Shobhit Goel <i>The University of Tokyo, Japan</i>	
ORAL ConfCode - 162	Quantum Materials and Spintronics	Layered FeGe₂ films on GaAs(001) substrates Presenter: Jens Herfort <i>Paul-Drude-Institute Berlin, Germany</i>	
ORAL ConfCode - 163	Quantum Materials and Spintronics	Epitaxial Growth of Cr based 2D Ferromagnets Presenter: Akhil Rajan <i>University of St Andrews, UK</i>	
ORAL ConfCode - 164	Quantum Materials and Spintronics	Epitaxial Growth and Quantum Transport of High-Mobility Elemental Topological Dirac Semimetal α-Sn Presenter: Le Duc Ahn <i>The university of Tokyo, Japan</i>	
ORAL ConfCode - 165	Quantum Materials and Spintronics	Analyzing layer-by-layer properties of MBE-grown multilayer structures via in-situ Spectroscopic Ellipsometry Presenter: Frank Peiris <i>Kenyon College, USA</i>	
ORAL - OSMAw ConfCode - 166	Quantum Materials and Spintronics	Quaternary-alloy ferromagnetic semiconductor (In,Ga,Fe)Sb Presenter: Tomoki Hotta <i>University of Tokyo, Japan</i>	
ORAL ConfCode - 167	Quantum Materials and Spintronics	InGaAs Based Tunnelling Diodes Barrier and Spacer Layer Structure by Grown Gas Sources Molecular Beam Epitaxy Presenter: Fauzia Jabeen <i>University of Würzburg, Germany</i>	
ORAL ConfCode - 168	Quantum Materials and Spintronics	Polaron-Polariton Device for Studying Spin Reversal of a Quantum Hall Ferromagnet Presenter: Stefan Fält <i>ETH Zurich, Switzerland</i>	
ORAL - OSMAw ConfCode - 169	Quantum Materials and Spintronics	Ferromagnetic Zinc-Blende FeAs epitaxially grown on GaAs (111)B substrates with very high Curie Temperature Presenter: Sriharsha Karumuri <i>University of Tokyo, Japan</i>	

ORAL - OSMAw ConfCode - 170	Quantum Materials and Spintronics	Controlled incorporation of Mn into Sb₂Te₃ using molecular beam epitaxy to grow magnetic topological insulators Presenter: Ido Levy <i>City College of New York, USA</i>	
ORAL - OSMAw ConfCode - 171	Quantum Materials and Spintronics	Transport Properties of MnSb₂Te₄ Ferromagnetic Layers Grown by MBE Presenter: Candice Forrester <i>The Graduate Center (CUNY), USA</i>	
POSTER - OSMAw ConfCode - 172	Quantum Materials and Spintronics	Polymorph control of monolayer NbSe₂ grown via MBE Presenter: Kaycee Underwood <i>University of St. Andrews, Scotland</i>	
POSTER - OSMAw ConfCode - 173	Quantum Materials and Spintronics	Isotopically engineered MBE growth of strained ²⁸Si for quantum circuits Presenter: Yujia Liu <i>Institut für Kristallzüchtung, Germany</i>	

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